

Field Effect Transistors

■ GaAs MES(Metal Semiconductor) FETs

● For V/UHF

Application	Type No.	Absolute Maximum Ratings (Ta =25 °C)				Electrical Characteristics (Ta =25 °C)						Package	
		V _{DS} (V)	V _{G1S} * V _{GS} (V)	V _{G2S} (V)	P _D (mW)	PG typ. (dB)	NF typ. (dB)	PG, NF Conditions					
								V _{DS} (V)	V _{G2} (V)	I _D (mA)	f (GHz)	No.	
UHF RF	3SK241	13	-6	-6	200	19	1.5	5	1.5	10	0.8	Mini Type (4 pins)	D11(a)
	3SK272	13	-6	-6	150	16	1.8	5	1.5	10	0.8	S Mini Type (4 pins)	D6
	3SK273	13	-6	-6	200	16	1.8	5	1.5	10	0.8	Mini Type (4 pins)	D11(a)
	△3SK287	13	-6	-6	200	13	2.1	5	1.5	10	0.8	Mini Type (4 pins)	D11(a)
	△3SK282	10	-6	-6	200	17	1.6	5	1.5	10	0.8	Mini Type (4 pins)	D11(a)
Power Amp.	2SK690	10	* -6	-	1W	15	P ₀ =25dBm	6	-	100	1	Mini Power Type	D15

△Preliminary

● For SHF

Application	Type No.	V _{DS} (V)	V _{GS} (V)	P _D (mW)	APG(dB)		NF(dB)		Package		
					f =4GHz	f =12GHz	f =4GHz	f =12GHz			
SHF	HEMT	2SK1962	3.5	-4	200	-	12	-	0.6	Ceramic Cross (4 pins)	D37(a)
		2SK1963	3.5	-4	200	-	12	-	0.5	Ceramic Cross (4 pins)	D37(a)
		2SK1964	3.5	-4	200	-	12	-	0.8	Ceramic Cross (4 pins)	D37(a)
	2nd. RF OSC.	2SK649 (X)	6	-6	200	13	6	< 1.4	4.5	Ceramic Cross (4 pins)	D37(b)